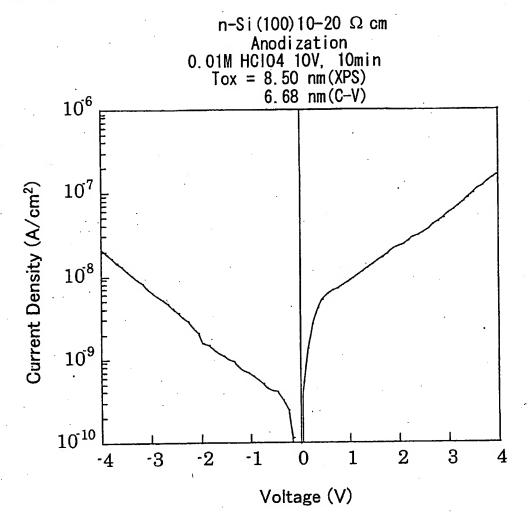
FIG. 16





n-Si(100)10-20Ωcm Anodization 1M HN03, 20V, 60min N2 anneal 600oC, 60min Tox = 9.7-10.4 nm(C-V) 11.2 nm(Ellipso)

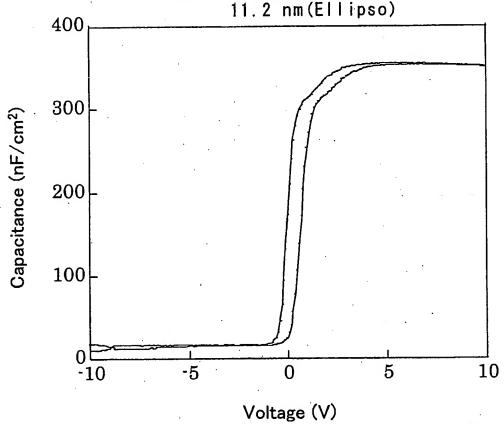


FIG. 19

